

FEATURES

Broadband frequency range: 0.1 GHz to 8 GHz

Nonreflective 50 Ω design

Low insertion loss: 1.7 dB at 6 GHz

High isolation: 36 dB at 6 GHz

High input linearity at 250 MHz to 8 GHz

P1dB: 28 dBm typical

IP3: 44 dBm typical

Integrated 2 to 4 line decoder

16-lead, 3 mm \times 3 mm LFCSP package

ESD HBM rating: 250 V (Class 1A)

ENHANCED PRODUCT FEATURES

Supports defense and aerospace applications (AQEC standard)

Military temperature range (-55°C to $+125^{\circ}\text{C}$)

Controlled manufacturing baseline

One assembly/test site

Product change notification

Qualification data available on request

APPLICATIONS

Broadband telecommunications systems

Fiber optics

Switched filter banks

Wireless Infrastructure below 8 GHz

GENERAL DESCRIPTION

The HMC344ATCPZ-EP is a broadband, nonreflective, single-pole, four-throw (SP4T) switch manufactured using a gallium arsenide (GaAs) metal semiconductor field effect transistor (MESFET) process. This switch offers high isolation, low insertion loss, and on-chip termination of the isolated ports.

The switch operates with a negative supply voltage (V_{EE}) range of -5 V to -3 V and requires two negative logic control voltages.

FUNCTIONAL BLOCK DIAGRAM

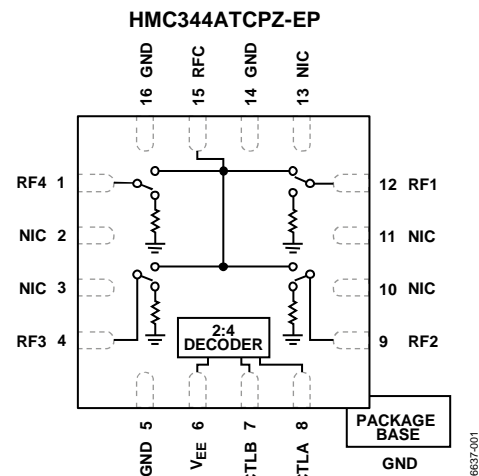


Figure 1.

The HMC344ATCPZ-EP includes an on-chip, binary two-line to four-line decoder that provides logic control from two logic input lines.

The HMC344ATCPZ-EP comes in a 3 mm \times 3 mm, 16-lead LFCSP package and operates from a 0.1 GHz to 8 GHz frequency range.

Additional application and technical information can be found in the [HMC344ALP3E](#) data sheet.

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REVISION HISTORY

3/2018—Revision 0: Initial Version

SPECIFICATIONS

$V_{EE} = -3\text{ V}$ or -5 V , control voltage (V_{CTL}) = 0 V or V_{EE} , case temperature (T_{CASE}) = 25°C , $50\ \Omega$ system, unless otherwise noted.

Table 1.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
FREQUENCY RANGE	f		0.1		8	GHz
INSERTION LOSS						
Between RFC and RF1 to RF4 (On)		0.1 GHz to 2 GHz		1.4	2.0	dB
		2 GHz to 4 GHz		1.4	2.0	dB
		4 GHz to 6 GHz		1.7	2.2	dB
		6 GHz to 8 GHz		2.1	2.5	dB
ISOLATION						
Between RFC and RF1 to RF4 (Off)		0.1 GHz to 2 GHz	39	43		dB
		2 GHz to 4 GHz	33	37		dB
		4 GHz to 6 GHz	32	36		dB
		6 GHz to 8 GHz	28	32		dB
RETURN LOSS						
RFC and RF1 to RF4 (On)		0.1 GHz to 2 GHz	12	16		dB
		2 GHz to 4 GHz	12	16		dB
		4 GHz to 6 GHz	11	16		dB
		6 GHz to 8 GHz	6	11		dB
RF1 to RF4 (Off)		0.1 GHz to 8 GHz	11	16		dB
SWITCHING						
Rise and Fall Time	t_{RISE}, t_{FALL}	10% to 90% of radio frequency (RF) output		35		ns
On and Off Time	t_{ON}, t_{OFF}	50% V_{CTL} to 90% of RF output		75		ns
INPUT LINEARITY ¹						
1 dB Power Compression	P1dB	f = 250 MHz to 8 GHz $V_{EE} = -5\text{ V}$ $V_{EE} = -3\text{ V}$	23	28 25		dBm dBm
Third-Order Intercept	IP3	10 dBm per tone, 1 MHz spacing $V_{EE} = -5\text{ V}$ $V_{EE} = -3\text{ V}$	40	44 44		dBm dBm
SUPPLY						
Voltage	V_{EE}	V_{EE} pin	-5		-3	V
Current	I_{EE}			2.5	6	mA
DIGITAL CONTROL INPUTS						
Voltage	V_{CTL}	CTLA and CTLB pins				
Low	V_{INL}	$V_{EE} = -5\text{ V}$ $V_{EE} = -3\text{ V}$	-3 -1		0 0	V V
High	V_{INH}	$V_{EE} = -5\text{ V}$ $V_{EE} = -3\text{ V}$	-5 -3		-4.2 -2.2	V V
Current	I_{CTL}					
Low	I_{INL}			40		μA
High	I_{INH}			0.10		μA
OPERATING TEMPERATURE			-55		+125	$^{\circ}\text{C}$

¹ Input linearity performance degrades at frequencies less than 250 MHz.

ABSOLUTE MAXIMUM RATINGS

For recommended operating conditions, see Table 1.

Table 2.

Parameter	Rating
Negative Supply Voltage (V_{EE})	-7 V
Digital Control Input Voltage Range	$V_{EE} - 0.5$ V to +1 V
RF Input Power (See Figure 2)	
$f = 250$ MHz to 8 GHz, $T_{CASE} = 85^{\circ}\text{C}$	
$V_{EE} = -5$ V	
Through Path	31 dBm
Terminated Path	26.5 dBm
Hot Switching	22 dBm
$V_{EE} = -3$ V	
Through Path	28 dBm
Terminated Path	23.5 dBm
Hot Switching	19 dBm
Temperature	
Junction, T_J	150°C
Storage	-65°C to $+150^{\circ}\text{C}$
Reflow	260°C
Junction to Case Thermal Resistance, θ_{JC}	
Through Path	107°C/W
Terminated Path	137°C/W
Electrostatic Discharge (ESD) Sensitivity	
Human Body Model (HBM)	250 V (Class 1A)

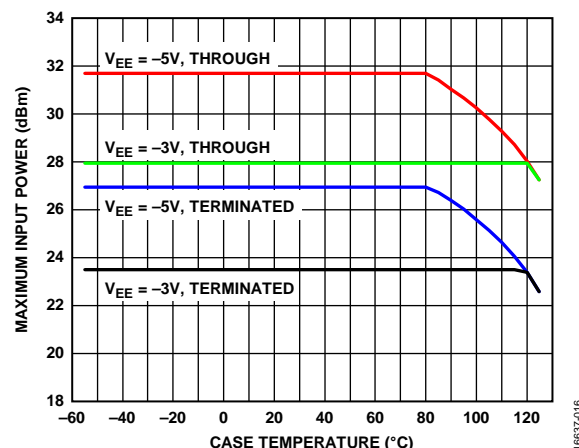


Figure 2. Maximum Input Power vs. Case Temperature Plot

ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

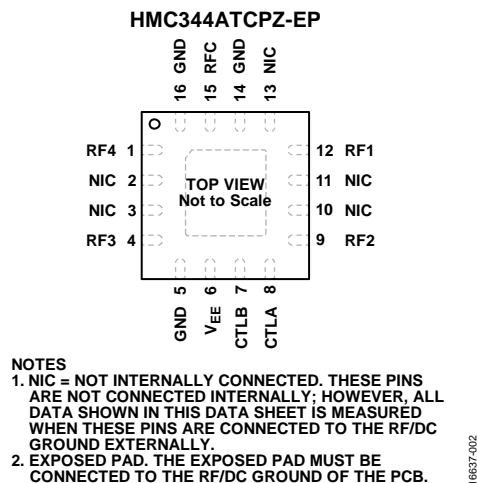


Figure 3. Pin Configuration

Table 3. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	RF4	RF4 Port. This pin is dc-coupled and matched to 50 Ω . A dc blocking capacitor is required if the RF line potential does not equal 0 V dc.
2, 3, 10, 11, 13	NIC	Not Internally Connected. These pins are not connected internally; however, all data shown in this data sheet is measured when these pins are connected to the RF/dc ground externally.
4	RF3	RF3 Port. This pin is dc-coupled and matched to 50 Ω . A dc blocking capacitor is required if the RF line potential does not equal 0 V dc.
5, 14, 16	GND	Ground. These pins connect to the RF/dc ground of the PCB.
6	V _{EE}	Negative Supply Voltage Pin.
7	CTLB	Control Input 2 Pin. See Table 4 for the control voltage truth table.
8	CTLA	Control Input 1 Pin. See Table 4 for the control voltage truth table.
9	RF2	RF2 Port. This pin is dc-coupled and matched to 50 Ω . A dc blocking capacitor is required if the RF line potential does not equal 0 V dc.
12	RF1	RF1 Port. This pin is dc-coupled and matched to 50 Ω . A dc blocking capacitor is required if the RF line potential does not equal 0 V dc.
15	RFC	RF Common Port. This pin is dc-coupled and matched to 50 Ω . A dc blocking capacitor is required if the RF line potential does not equal 0 V dc.
	EPAD	Exposed Pad. The exposed pad must be connected to the RF/dc ground of the PCB.

Table 4. Control Voltage Truth Table

Digital Control Input		RF Paths			
CTLA	CTLB	RFC to RF1	RFC to RF2	RFC to RF3	RFC to RF4
High	High	Insertion loss (on)	Isolation (off)	Isolation (off)	Isolation (off)
Low	High	Isolation (off)	Insertion loss (on)	Isolation (off)	Isolation (off)
High	Low	Isolation (off)	Isolation (off)	Insertion loss (on)	Isolation (off)
Low	Low	Isolation (off)	Isolation (off)	Isolation (off)	Insertion loss (on)

INTERFACE SCHEMATICS

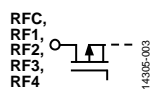


Figure 4. RFC and RF1 to RF4 Interface Schematic

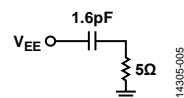
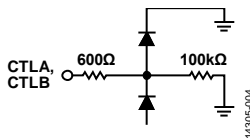
Figure 6. V_{EE} Interface Schematic

Figure 5. CTLA and CTLB Interface Schematic

TYPICAL PERFORMANCE CHARACTERISTICS

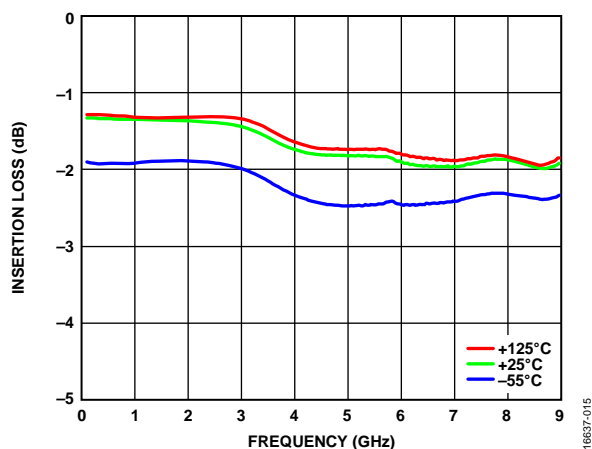


Figure 7. Insertion Loss vs. Frequency at Various Temperatures, Between RFC and RF1

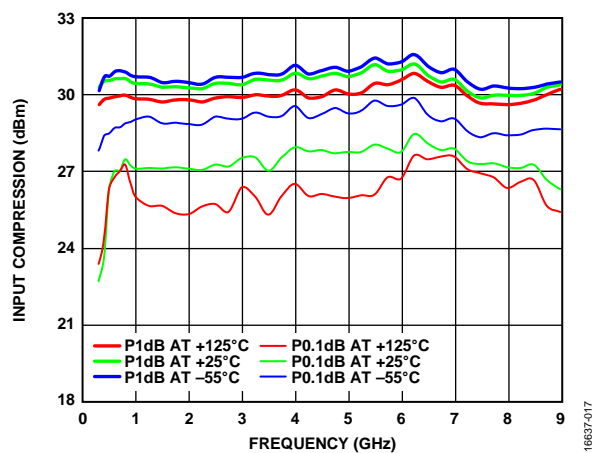


Figure 8. Input Compression vs. Frequency at Various Temperatures, $V_{EE} = -5\text{ V}$

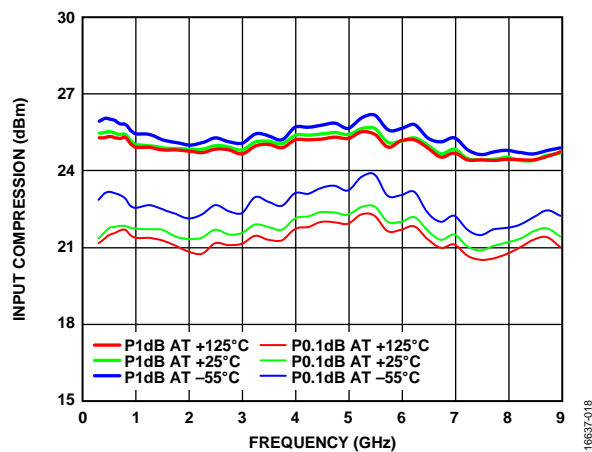
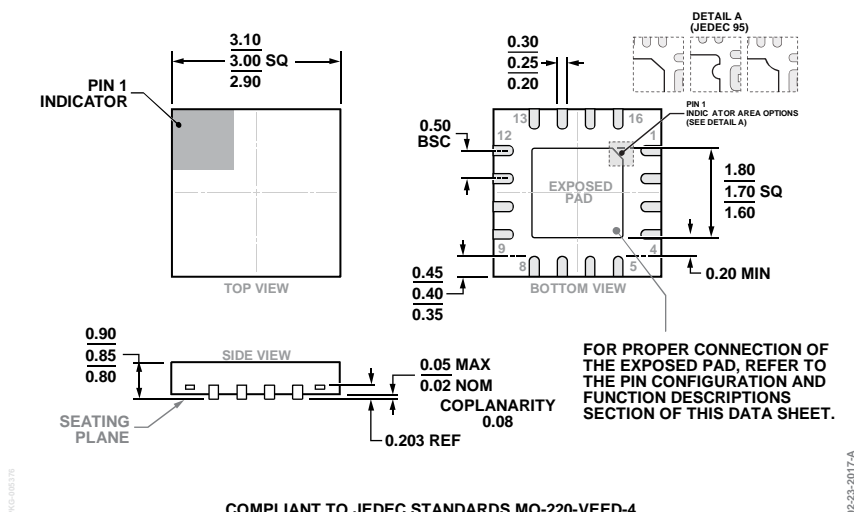


Figure 9. Input Compression vs. Frequency at Various Temperatures, $V_{EE} = -3\text{ V}$

OUTLINE DIMENSIONS



ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
HMC344ATCPZ-EP-PT	−55°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-51
HMC344ATCPZ-EP-R7	−55°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16-51

¹ All models are RoHS compliant parts.